

Features

- LOW POWER STANDBY
- LOW POWER OPERATION
- DATA RETENTION
- TTL COMPATIBLE INPUT/OUTPUT
- COMMON DATA IN/OUT
- THREE-STATE OUTPUTS
- STANDARD JEDEC PINOUT
- FAST ACCESS TIME
- MILITARY TEMPERATURE RANGE
- INDUSTRIAL TEMPERATURE RANGE
- 18 PIN PACKAGE FOR HIGH DENSITY
- ON CHIP ADDRESS REGISTER

250 μ W MAX.
35mW/MHz MAX.
@ 2.0V MIN.

200nsec MAX.

Description

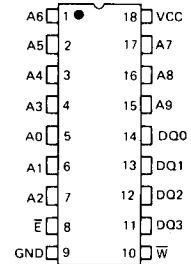
The HM-6514 is a 1024 x 4 static CMOS RAM fabricated using self aligned silicon gate technology. The device utilizes synchronous circuitry to achieve high performance and low power operation.

On chip latches are provided for the addresses allowing efficient interfacing with microprocessor systems. The data output can be forced to a high impedance state for use in expanded memory systems.

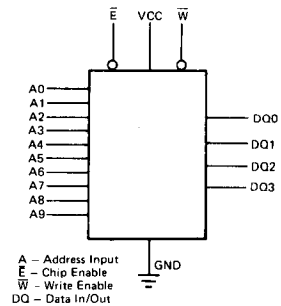
The HM-6514 is a fully static RAM and may be maintained in any state for an indefinite period of time. Data retention supply voltage and supply current are guaranteed over temperature.

Pinout

TOP VIEW

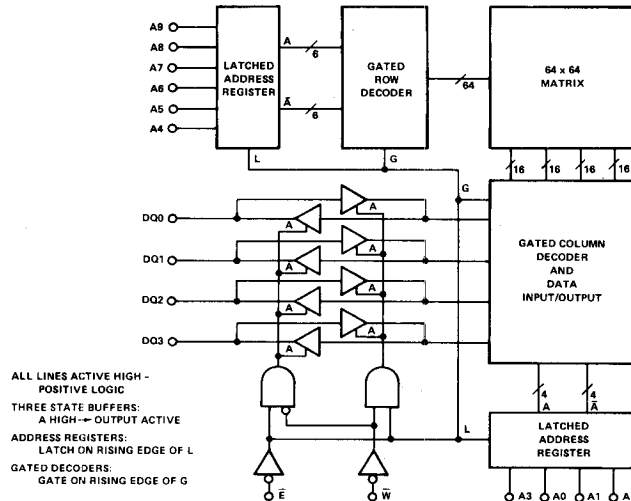


Logic Symbol



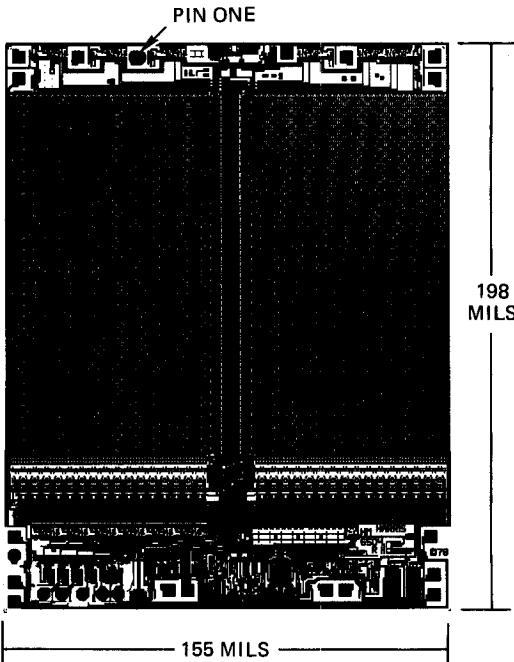
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Functional Diagram



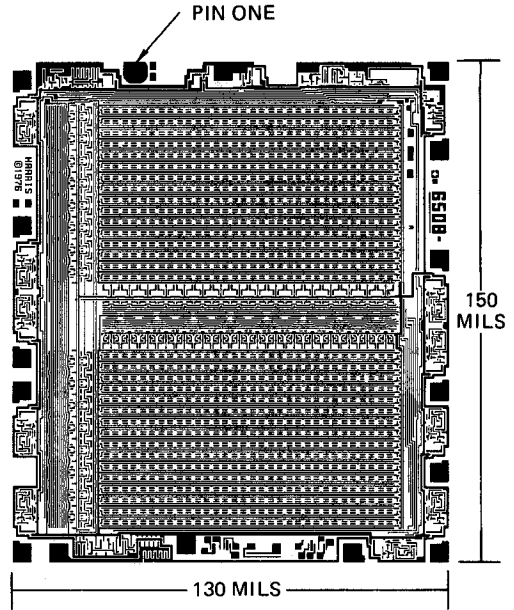
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HM-6505



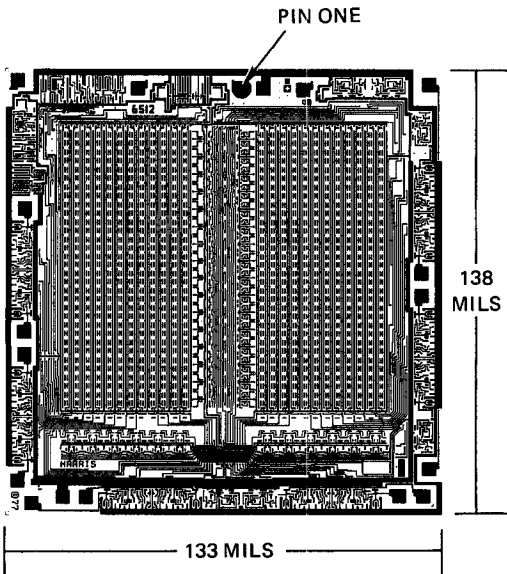
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HM-6508



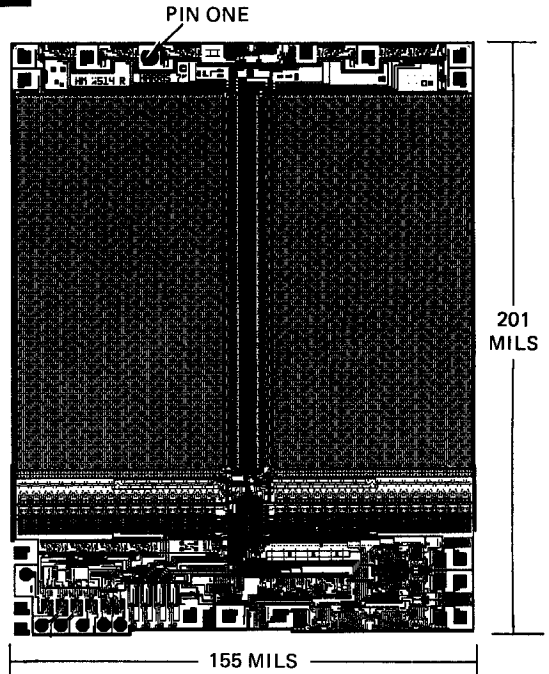
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HM-6512



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HM-6513, HM-6514



NOTE: OCTAGONAL PADS ARE NOT FOR BONDING.